

## Product features

High precision machining technology  
Low temperature drift, high power.  
Ceramic substrate, 50  $\Omega$  coplanar waveguide  
Gold wire bonding

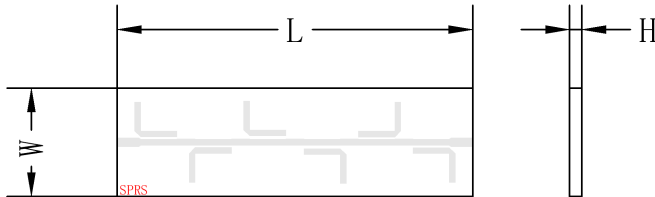
## Tech specifications

Items	Parameters	Units
Passband	DC-3.2	GHz
带宽通带	4.0-12.0	GHz
损耗通带	3.0	dB
Ripple	3.0	dB
VSWR	2.0:1	
Group delay ripple	0.8	ns
Rejection	30@3.6GHz	dBc

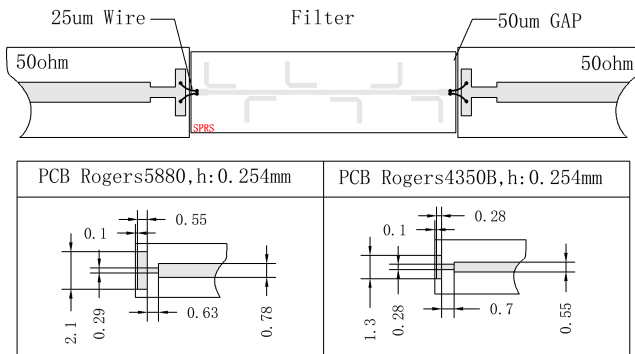
## Other requirement (Design assurance)

power	1W CW
Work Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:13.9 , W:4.0 , h:0.26

## Outline drawing: Port centered



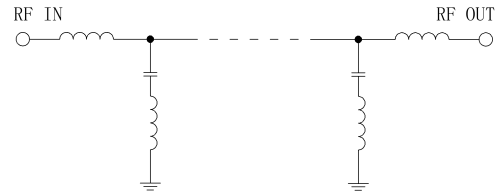
## Suggested PCB Layout



## Note

- 1: 0.1mm from the side wall, 1.75mm from the surface to the upper cover.
- 2: Suggest using conductive adhesive for bonding;
- 3: The chip should be installed on kovar alloy or molybdenum copper;
- 4: Suggest using a T-shaped structure for microstrip bonding.

## Schematic diagram



## Typical test curve

